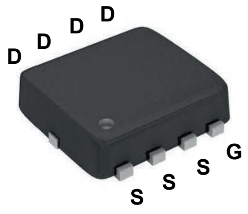
GOOD-ARK
SEMICONDUCTOR

GSGN8R77

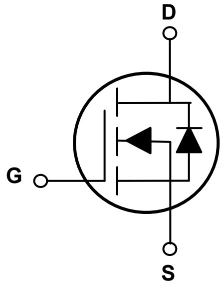
80V N-Channel MOSFET

Main Product Characteristics

BV_{DSS}	80V
$R_{DS(ON)}$	6.3mΩ (Typ.)
I_D	77A



PPAK3x3



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery

Description

The GSGN8R77 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supplies and a wide variety of other applications.

Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	80	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	77	A
Drain Current-Continuous (T_C=100°C)		48	A
Pulsed Drain Current	I_{DM}	308	A
Maximum Power Dissipation	P_D	75	W
Derating Factor		0.6	W/°C
Single Pulse Avalanche Energy[1]	E_{AS}	231	mJ
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.66	°C/W
Operating Junction and Storage Temperature Range	T_J/T_{STG}	-55 To +150	°C

Electrical Characteristics (T_C=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On / Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250μA	80	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=80V, V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	2	3.3	4	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=20A	-	6.3	7.5	mΩ
Forward Transconductance	gfs	V_{DS}=10V, I_D=20A	-	45	-	S
Dynamic and Switching Characteristics						
Input Capacitance	C_{iss}	V_{DS}=40V, V_{GS}=0V, F=1.0MHz	-	1420	-	pF
Output Capacitance	C_{oss}		-	775.8	-	
Reverse Transfer Capacitance	C_{rss}		-	26.9	-	
Turn-on Delay Time[2]	$t_{d(on)}$	V_{DD}=40V, I_D=20A, V_{GS}=10V, R_G=3Ω	-	9.1	-	nS
Turn-on Rise Time[2]	t_r		-	4.7	-	
Turn-Off Delay Time[2]	$t_{d(off)}$		-	20	-	
Turn-Off Fall Time[2]	t_f		-	5	-	
Total Gate Charge[2]	Q_g	V_{DS}=40V, I_D=20A, V_{GS}=10V	-	23.9	-	nC
Gate-Source Charge[2]	Q_{gs}		-	9.1	-	
Gate-Drain Charge[2]	Q_{gd}		-	5.2	-	
Source-Drain Ratings and Characteristics						
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=20A	-	-	1.2	V
Diode Forward Current	I_S	-	-	-	77	A
Reverse Recovery Time	T_{rr}	T_J=25°C, I_F=20A, di/dt=100A/μs	-	50	-	nS
Reverse Recovery Charge	Q_{rr}		-	74	-	nC

Notes:

1. Eas condition: T_J=25°C, V_{DD}=40V, V_G=10V, L=0.5mH, R_g=25Ω.
2. Guaranteed by design, not subject to production.
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150°C. The SOA curve provides a single pulse rating.

Typical Electrical and Thermal Characteristic Curves

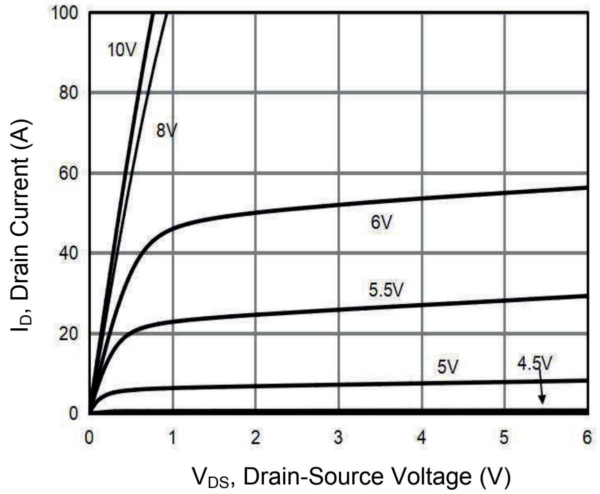


Figure 1. Output Characteristics

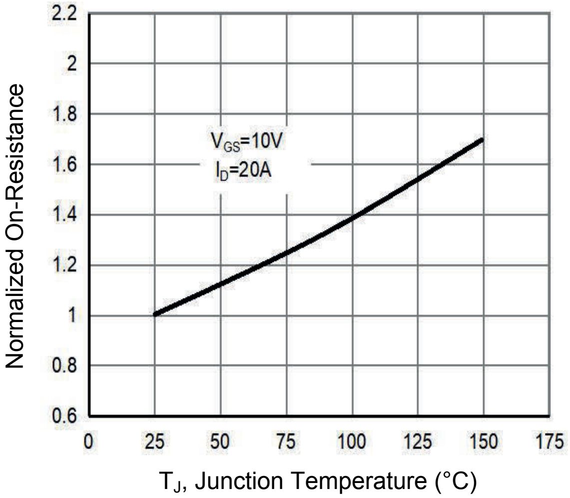


Figure 2. $R_{DS(ON)}$ vs. Junction Temperature

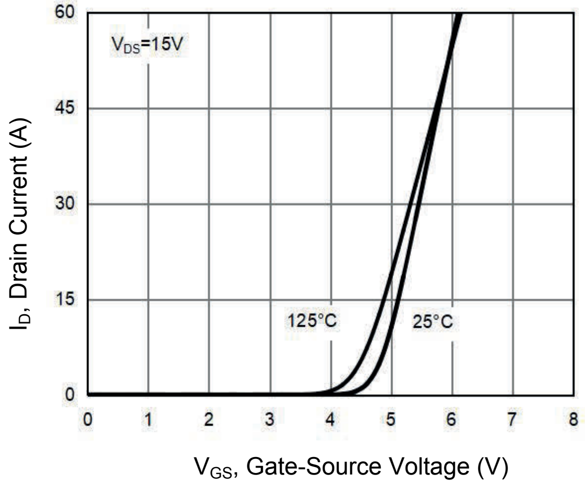


Figure 3. Transfer Characteristics

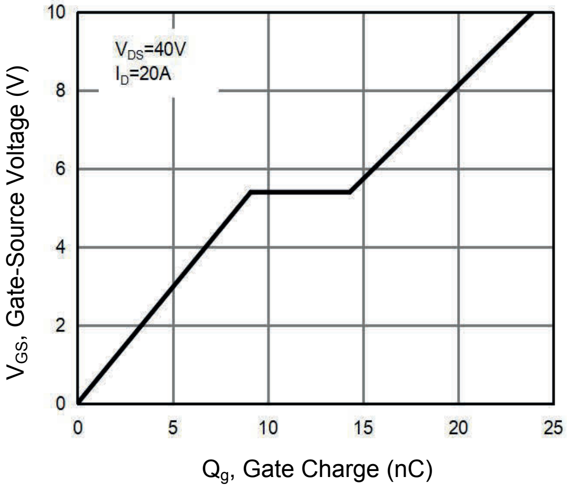


Figure 4. Gate Charge

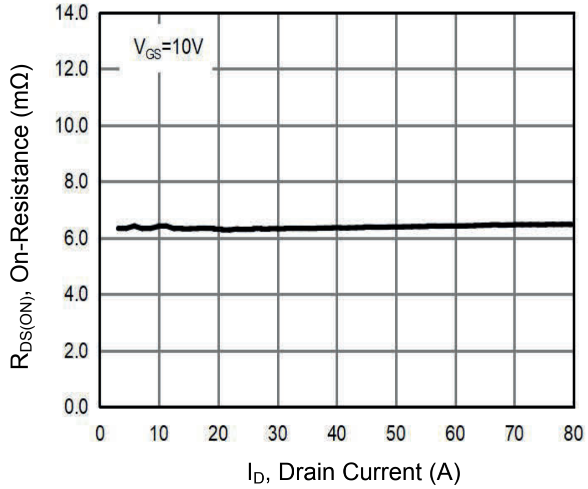


Figure 5. $R_{DS(ON)}$ vs. Drain Current

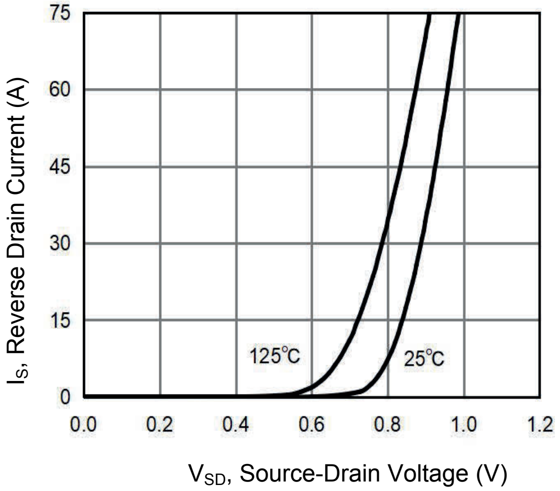


Figure 6. Source-Drain Diode Forward Voltage

Typical Electrical and Thermal Characteristic Curves

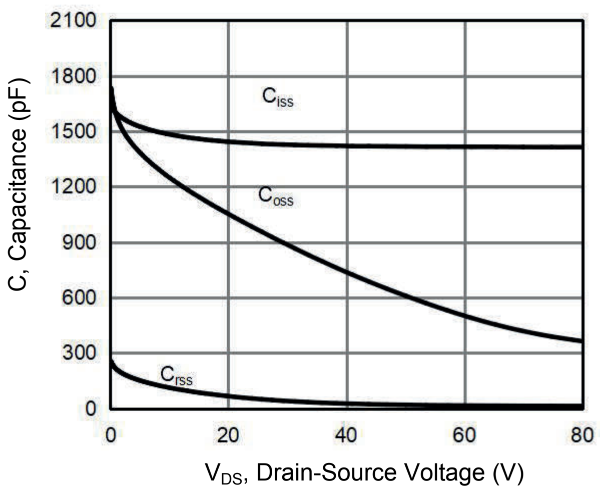


Figure 7. Capacitance vs. V_{DS}

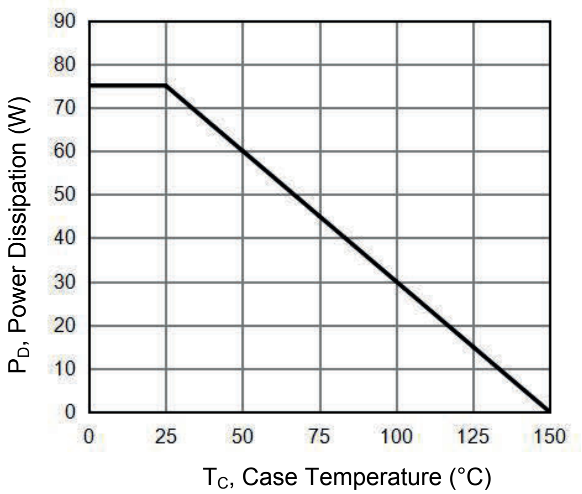


Figure 8. Power De-rating

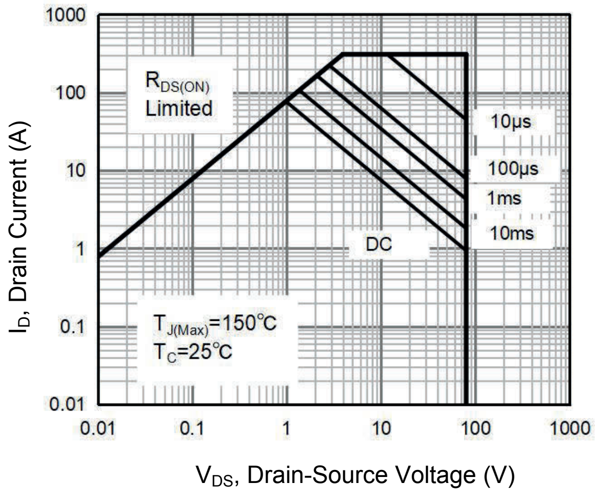


Figure 9. Safe Operation Area[3]

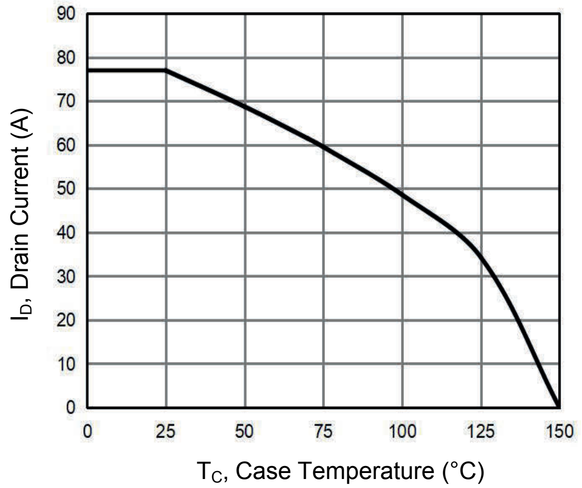


Figure 10. Current De-rating

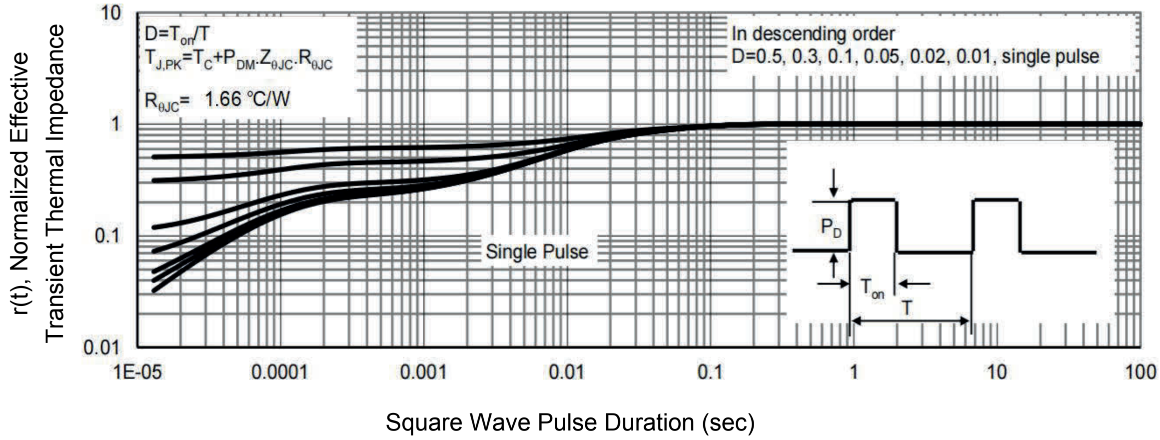
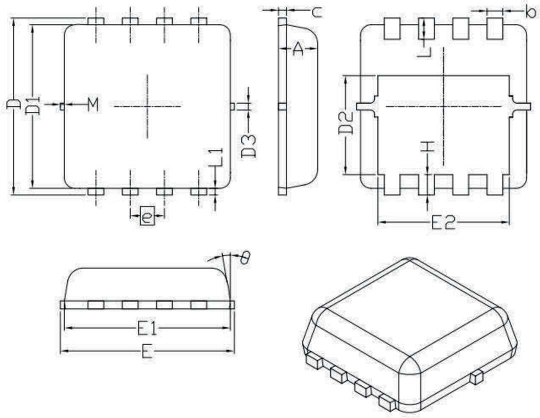


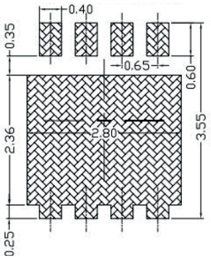
Figure 11. Normalized Maximum Transient Thermal Impedance

Package Outline Dimensions (PPAK3x3)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.70	0.80	0.028	0.031
b	0.25	0.35	0.010	0.014
c	0.10	0.25	0.004	0.010
D	3.25	3.45	0.128	0.136
D1	3.00	3.20	0.118	0.126
D2	1.78	1.98	0.070	0.078
D3	0.13 NOM		0.005 NOM	
E	3.10	3.30	0.122	0.130
E1	3.00	3.20	0.118	0.126
E2	2.39	2.59	0.094	0.102
e	0.65 BSC		0.026 BSC	
H	0.30	0.50	0.012	0.020
L	0.30	0.50	0.012	0.020
L1	0.13 NOM		0.005 NOM	
θ	-	12°	-	12°
M	-	0.15	-	0.006

Recommended Pad Layout



unit: mm

Order Information

Device	Package	Marking	Packaging	SPQ
GSGN8R77	PPAK3x3	N8R77	Tape & Reel	5,000 pcs / Reel

For more information, please contact us at: inquiry@goodarksemi.com